

First-In First-Out (FIFO) Buffer Memory

The 74F433 is an expandable fall-through type high-speed First-In First-Out (FIFO) Buffer Memory that is optimized for high-speed disk or tape controller and communication buffer applications. It is organized as 64-words by 4-bits and may be expanded to any number of words or any number of bits in multiples of four. Data may be entered or extracted asynchronously in serial or parallel, allowing economical implementation of buffer memories.

The 74F433 has 3-STATE outputs that provide added versatility, and is fully compatible with all TTL families.

Quality Overview Rochester Electronics Manufactured Components • ISO-9001 AS9120 certification Rochester branded components are Qualified Manufacturers List (QML) MIL-PRF-38535 manufactured using either die/wafers Class Q Military purchased from the original suppliers Class V Space Level or Rochester wafers recreated from the Qualified Suppliers List of Distributors (QSLD) original IP. All recreations are done with · Rochester is a critical supplier to DLA and the approval of the OCM. meets all industry and DLA standards. Parts are tested using original factory Rochester Electronics, LLC is committed to supplying test programs or Rochester developed test solutions to guarantee product

products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

meets or exceeds the OCM data sheet.

April 1988 Revised October 2000 74F433 First-In First-Out (FIFO) Buffer Memory

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General Description

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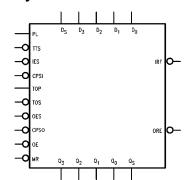
Features

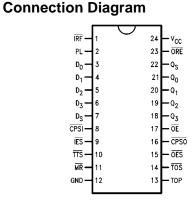
- Serial or parallel input
- Serial or parallel output
- Expandable without additional logic
- 3-STATE outputs
- Fully compatible with all TTL families
- Slim 24-pin package
- 9423 replacement

Ordering Code:

Order Number	Package Number	Package Description
74F433SPC	N24C	24-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300 Wide

Logic Symbol



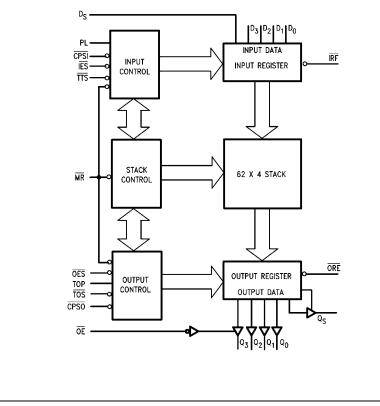


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Unit Loading/Fan Out

Pin Names	Description	U.L.	Input I _{IH} /I _{IL}		
Pin Names	Description	HIGH/LOW	Output I _{OH} /I _{OL}		
PL	Parallel Load Input	1.0/0.66	20 μΑ/400 μΑ		
CPSI	Serial Input Clock	1.0/0.66	20 μΑ/400 μΑ		
IES	Serial Input Enable	1.0/0.66	20 μA/400 μA		
TTS	Transfer to Stack Input	1.0/0.66	20 μA/400 μA		
MR	Master Reset	1.0/0.66	20 μA/400 μA		
OES	Serial Output Enable	1.0/0.66	20 μA/400 μA		
ТОР	Transfer Out Parallel	1.0/0.66	20 μA/400 μA		
TOS	Transfer Out Serial	1.0/0.66	20 μA/400 μA		
CPSO	Serial Output Clock	1.0/0.66	20 μA/400 μA		
OE	Output Enable	1.0/0.66	20 μA/400 μA		
D ₀ -D ₃	Parallel Data Inputs	1.0/0.66	20 μA/400 μA		
D _S	Serial Data Input	1.0/0.66	20 μA/400 μA		
Q ₀ –Q ₃	Parallel Data Outputs	285/10	5.7 mA/16 mA		
Q _S	Serial Data Output	285/10	5.7 μA/16 mA		
IRF	Input Register Full	20/5	400 µA/8 mA		
ORE	Output Register Empty	20/5	400 µA/8 mA		

Block Diagram



Functional Description

As shown in the block diagram, the 74F433 consists of three sections:

- An Input Register with parallel and serial data inputs, as well as control inputs and outputs for input handshaking and expansion.
- 2. A 4-bit-wide, 62-word-deep fall-through stack with selfcontained control logic.
- An Output Register with parallel and serial data outputs, as well as control inputs and outputs for output handshaking and expansion.

These three sections operate asynchronously and are virtually independent of one another.

Input Register (Data Entry)

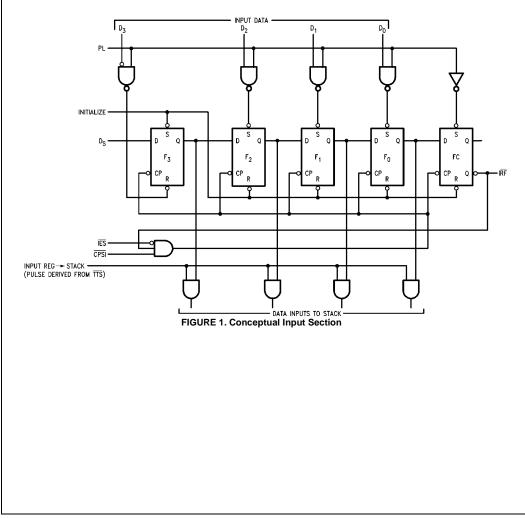
The Input Register can receive data in either bit-serial or 4bit parallel form. It stores this data until it is sent to the fallthrough stack, and also generates the necessary status and control signals.

This 5-bit register (see Figure 1) is initialized by setting flipflop F_3 and resetting the other flip-flops. The \overline{Q} -output of the last flip-flop (FC) is brought out as the Input Register Full (IRF) signal. After initialization, this output is HIGH.

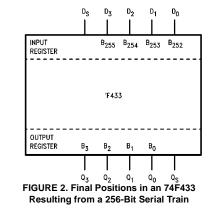
Parallel Entry—A HIGH on the Parallel Load (PL) input loads the D₀–D₃ inputs into the F_0 – F_3 flip-flops and sets the FC flip-flop. This forces the IRF output LOW, indicating that the input register is full. During parallel entry, the Serial Input Clock (CPSI) input must be LOW.

Serial Entry—Data on the Serial Data (D_S) input is serially entered into the shift register (F_3 , F_2 , F_1 , F_0 , FC) on each HIGH-to-LOW transition of the CPSI input when the Serial Input Enable (IES) signal is LOW. During serial entry, the PL input should be LOW.

After the fourth clock transition, the four data bits are located in flip-flops F₀–F₃. The FC flip-flop is set, forcing the $\overline{\text{IRF}}$ output LOW and internally inhibiting $\overline{\text{CPSI}}$ pulses from affecting the register. Figure 2 illustrates the final positions in an 74F433 resulting from a 256-bit serial bit train (B₀ is the first bit, B₂₅₅ the last).



Functional Description (Continued)



Fall-Through Stack—The outputs of flip-flops F_0-F_3 feed the stack. A LOW level on the Transfer to Stack (TTS) input initiates a fall-through action; if the top location of the stack is empty, data is loaded into the stack and the input register is re-initialized. (Note that this initialization is delayed until PL is LOW). Thus, automatic FIFO action is achieved by connecting the IRF output to the TTS input.

An RS-type flip-flop (the initialization flip-flop) in the control section records the fact that data has been transferred to the stack. This prevents multiple entry of the same word into the stack even though $\overline{\rm IRF}$ and $\overline{\rm TTS}$ may still be LOW; the initialization flip-flop is not cleared until PL goes LOW.

Once in the stack, data falls through automatically, pausing only when it is necessary to wait for an empty next location. In the 74F433, the master reset ($\overline{\text{MR}}$) input only initializes the stack control section and does not clear the data.

Output Register

The Output Register (see Figure 3) receives 4-bit data words from the bottom stack location, stores them, and outputs data on a 3-STATE, 4-bit parallel data bus or on a 3-STATE serial data bus. The output section generates and receives the necessary status and control signals.

Parallel Extraction—When the FIFO is empty after a LOW pulse is applied to the MR input, the Output Register Empty (\overline{ORE}) output is LOW. After data has been entered into the FIFO and has fallen through to the bottom stack location, it is transferred into the output register, if the Transfer Out Parallel (TOP) input is HIGH. As a result of the data transfer Out Parallel (TOP) input is HIGH.

fer, $\overline{\text{ORE}}$ goes HIGH, indicating valid data on the data outputs (provided that the 3-STATE buffer is enabled). The TOP input can then be used to clock out the next word.

When TOP goes LOW, ORE also goes LOW, indicating that the output data has been extracted; however, the data itself remains on the output bus until a HIGH level on TOP permits the transfer of the next word (if available) into the output register. During parallel data extraction, the serial output clock (CPSO) line should be LOW. The Transfer Out Serial (TOS) line should be grounded for single-slice operation or connected to the appropriate ORE line for expanded operation (refer to the "Expansion" section).

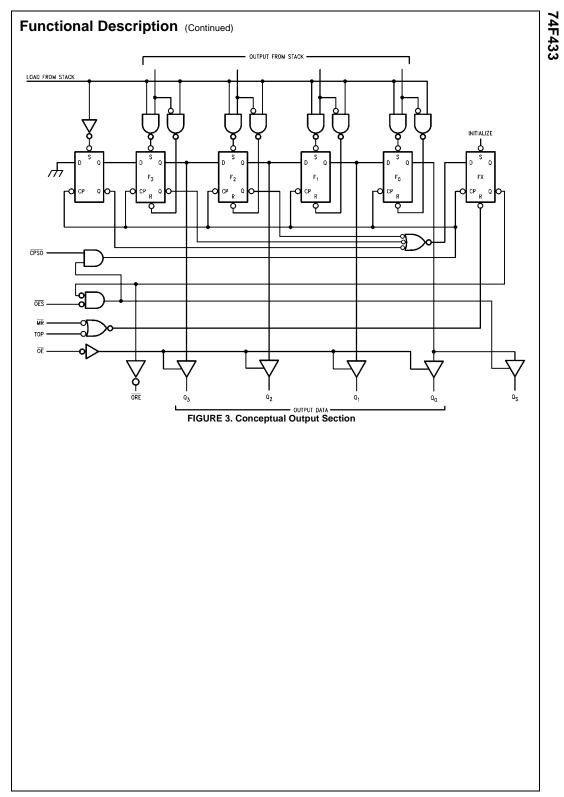
The TOP signal is not edge-triggered. Therefore, if TOP goes HIGH before data is available from the stack but data becomes available before TOP again goes LOW, that data is transferred into the output register. However, internal control circuitry prevents the same data from being transferred twice. If TOP goes HIGH and returns to LOW before data is available from the stack, ORE remains LOW, indicating that there is no valid data at the outputs.

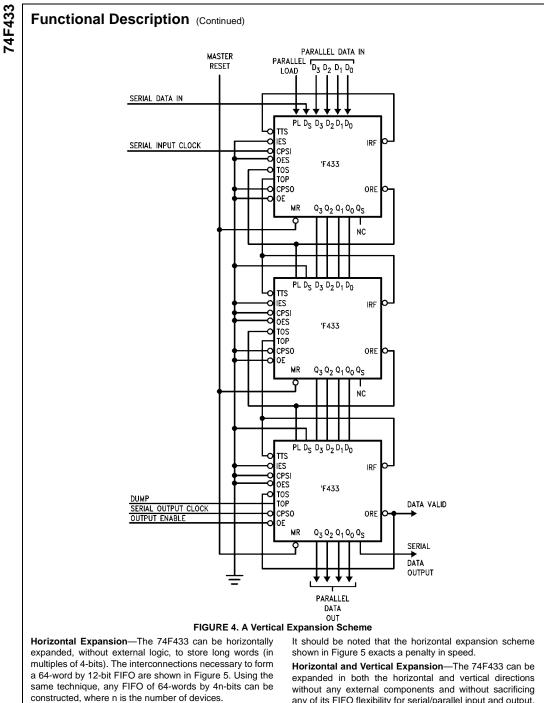
Serial Extraction—When the FIFO is empty after a LOW is applied to the MR input, the \overline{ORE} output is LOW. After data has been entered into the FIFO and has fallen through to the bottom stack location, it is transferred into the output register, if the \overline{TOS} input is LOW and TOP is HIGH. As a result of the data transfer, \overline{ORE} goes HIGH, indicating that valid data is in the register.

The 3-STATE Serial Data Output (Q_S) is automatically enabled and puts the first data bit on the output bus. Data is serially shifted out on the HIG<u>H-to-L</u>OW transition of CPSO. To prevent false shifting, CPSO should be LOW when the new word is being loaded into the output register. The fourth transition empties the shift register, forces ORE LOW, and disables the serial output, Q_S. For serial operation, the \overline{ORE} output may be tied to the \overline{TOS} input, requesting new word from the stack as soon as the previous one has been shifted out.

Expansion

Vertical Expansion—The 74F433 may be vertically expanded, without external components, to store more words. The interconnections necessary to form a 190-word by 4-bit FIFO are shown in Figure 4. Using the same technique, any FIFO of (63n+1)-words by 4-bits can be configured, where n is the number of devices. Note that expansion does not sacrifice any of the 74F433 flexibility for serial/parallel input and output.





The right-most (most significant) device is connected to the TTS inputs of all devices. Similarly, the ORE output of the most significant device is connected to the TOS inputs of all devices. As in the vertical expansion scheme, horizontal expansion does not sacrifice any of the 74F433 flexibility for serial/parallel input and output. Horizontal and Vertical Expansion—The 74F433 can be expanded in both the horizontal and vertical directions without any external components and without sacrificing any of its FIFO flexibility for serial/parallel input and output. The interconnections necessary to form a 127-word by 16bit FIFO are shown in Figure 6. Using the same technique, any FIFO of (63m+1)-words by 4n-bits can be configured, where m is the number of devices in a column and n is the number of devices in a row. Figure 7 and Figure 8 illustrate the timing diagrams for serial data entry and extraction for

Functional Description (Continued)

the FIFO shown in Figure 6. Figure 9 illustrates the final positions of bits in an expanded 74F433 FIFO resulting from a 2032-bit serial bit train.

Interlocking Circuitry—Most conventional FIFO designs provide status signal analogous to IRF and \overline{ORE} . However, when these devices are operated in arrays, variations in unit-to-unit operating speed require external gating to ensure that all devices have completed an operation. The 74F433 incorporates simple but effective 'master/slave' interlocking circuitry to eliminate the need for external gating.

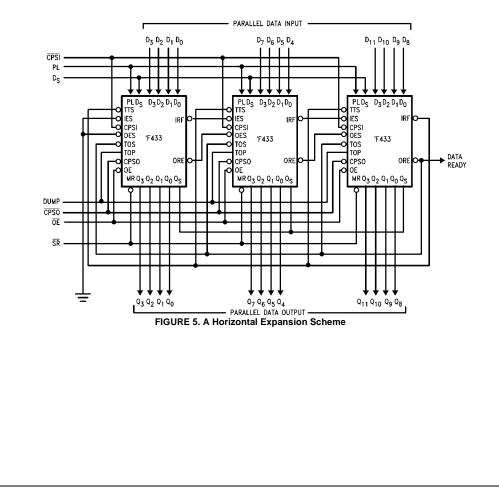
In the 74F433 array of Figure 6, devices 1 and 5 are the row masters; the other devices are slaves to the master in their rows. No slave in a given row initializes its input register until it has received a LOW on its IES input from a row master or a slave of higher priority.

Similarly, the $\overline{\text{ORE}}$ outputs of slaves do not go HIGH until their inputs have gone HIGH. This interlocking scheme ensures that new input data may be accepted by the array when the $\overline{\text{IRF}}$ output of the final slave in that row goes HIGH and that output data for the array may be extracted when the $\overline{\text{ORE}}$ output of the final slave in the output row goes HIGH.

The row master is established by connecting its $\overline{\text{IES}}$ input to ground, while a slave receives its $\overline{\text{IES}}$ input from the $\overline{\text{IRF}}$ output of the next-higher priority device. When an array of 74F433 FIFOs is initialized with a HIGH on the MR inputs of all devices, the $\overline{\text{IRF}}$ outputs of all devices are HIGH. Thus, only the row master receives a LOW on the $\overline{\text{IES}}$ input during initialization.

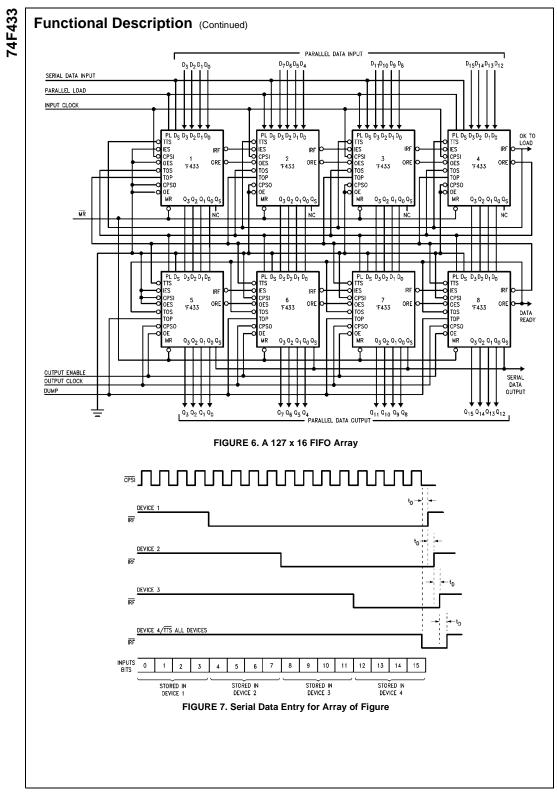
Figure 10 is a conceptual logic diagram of the internal <u>cir</u>cuitry that determines master/slave operation. When MR and IES are LOW, the master latch is set. When TTS goes LOW, the initialization flip-flop is set. If the master latch is HIGH, the input register is immediately initialized and the initialization flip-flop reset. If the master latch is register is not initialized until IES goes LOW. In array operation, activating TTS initiates a ripple input register initialization from the row master to the last slave.

A similar operation takes place for the output register. Either a \overline{TOS} or \underline{TOP} input initiates a load-from-stack operation and sets the \overline{ORE} request flip-flop. If the master latch is set, the last output register flip-flop is set and the \overline{ORE} line goes HIGH. If the master latch is reset, the \overline{ORE} output is LOW until a Serial Output Enable (\overline{OES}) input is received.

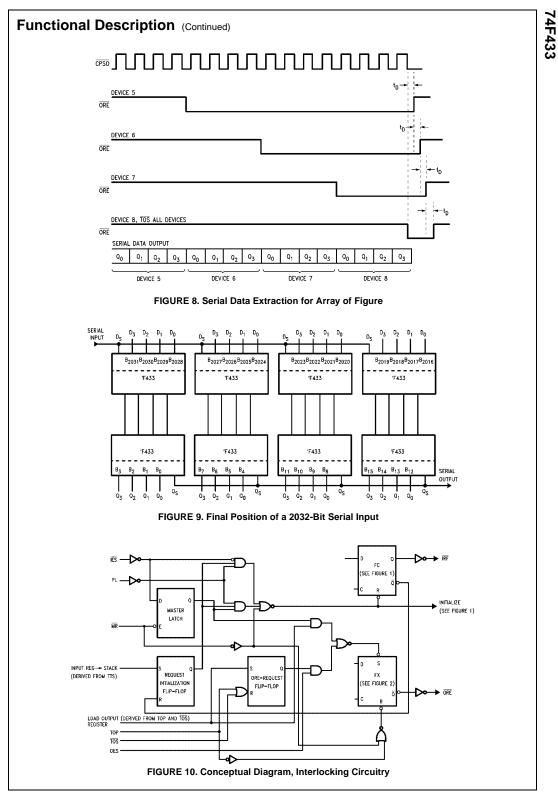


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74F433



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Absolute Maximum Ratings(Note 1)

Storage Temperature	$-65^{\circ}C$ to $+150^{\circ}C$
Ambient Temperature under Bias	$-55^{\circ}C$ to $+125^{\circ}C$
Junction Temperature under Bias	-55°C to +150°C
V _{CC} Pin Potential to	
Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to +7.0V
Input Current (Note 2)	-30 mA to +5.0 mA
Voltage Applied to Output	
in HIGH State (with $V_{CC} = 0V$)	
Standard Output	-0.5V to V _{CC}
3-STATE Output	-0.5V to +5.5V
Current Applied to Output	
in LOW State (Max)	twice the rated I_{OL} (mA)

Recommended Operating Conditions

Free Air Ambient Temp	erature
Supply Voltage	

0°C to +70°C +4.5V to +5.5V

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

DC Electrical Characteristics

Symbol	Parameter		Min	Тур	Max	Units	V _{cc}	Conditions
VIH	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal
VIL	Input LOW Voltage				0.8	V		Recognized as a LOW Signal
V _{CD}	Input Clamp Diode Voltage				-1.5	V	Min	I _{IN} = -18 mA
V _{OH}	Output HIGH	10% V _{CC}	2.4					$I_{OH} = 400 \ \mu A \ (\overline{ORE}, \ \overline{IRF})$
	Voltage	10% V _{CC}	2.4			v	Min	I _{OH} = 5.7 mA (Q _n , Q _s)
		$5\% V_{CC}$	2.7			v	IVIIN	$I_{OH} = 400 \ \mu A \ (\overline{ORE}, \ \overline{IRF})$
		5% V_{CC}	2.7					$I_{OH} = 5.7 \text{ mA} (Q_n, Q_s)$
V _{OL}	Output LOW Voltage	10% V _{CC}			0.50	V	Min	$I_{OL} = 16 \text{ mA} (Q_n, Q_s)$
IIH	Input HIGH Current				5.0	μΑ	Max	V _{IN} = 2.7V
I _{BVI}	Input HIGH Current				7.0	μA	Max	V _{IN} = 7.0V
	Breakdown Test				7.0	μΛ	IVIGA	VIN - 7.0V
I _{CEX}	Output HIGH				50	μA	Max	$V_{OUT} = V_{CC}$
	Leakage Current				00	μι	Max	•001 - •CC
V _{ID}	Input Leakage		4.75			V	0.0	$I_{ID} = 1.9 \ \mu A$
	Test		4.75			v	0.0	All Other Pins Grounded
I _{OD}	Output Leakage				3.75	μA	0.0	$V_{IOD} = 150 \text{ mV}$
	Circuit Current				0.70	μι	0.0	All Other Pins Grounded
IIL	Input LOW Current				-0.4	mA	Max	$V_{IN} = 0.5V$
I _{OZH}	Output Leakage Current				50	μΑ	Max	$V_{OUT} = 2.7V (Q_n, Q_s)$
I _{OZL}	Output Leakage Current				-50	μΑ	Max	$V_{OUT} = 0.5V (Q_n, Q_s)$
los	Output Short-Circuit Current		-20		-130	mA	Max	$V_{OUT} = 0V$
I _{CC}	Power Supply Current			150	215	mA	Max	

		T _A = -	⊦25°C	$T_A = 0^\circ C$	to +70°C	1	
		V _{CC} =	+5.0V	V _{cc} =	+5.0V		Figure Number
Symbol	Parameter	C _L =			50 pF	Units	
		Min	Max	Min	Max		
t _{PHL}	Propagation Delay, Negative-Going	2.0	17.0	2.0	10.0		
	CPSI to IRF Output	2.0	17.0	2.0	18.0	ns	Figures
t _{PLH}	Propagation Delay, Negative-Going TTS to IRF	9.0	34.0	8.0	38.0	10	11, 12
t _{PLH}	Propagation Delay, Negative-Going	4.0	25.0	3.0	27.0	ns	Figures
t _{PHL}	CPSO to Q _S Output	5.0	20.0	5.0	21.0		13, 14
t _{PLH}	Propagation Delay, Positive-Going	8.0	35.0	7.0	38.0	ns	Figure 15
t _{PHL}	TOP to Q ₀ –Q ₃ Outputs	7.0	30.0	7.0	32.0		Ű
t _{PHL}	Propagation Delay, Negative-Going CPSO to ORE	7.0	25.0	6.0	28.0	ns	Figures 13, 14
t _{PHL}	Propagation Delay, Negative-Going TOP to ORE	6.0	26.0	6.0	28.0	- ns	Figure 15
t _{PLH}	Propagation Delay, Positive-Going TOP to ORE	13.0	48.0	12.0	51.0		rigure is
t _{PLH}	Propagation Delay, Negative-Going TOS to Positive-Going ORE	13.0	45.0	12.0	50.0	ns	Figures 13, 14
t _{PHL}	Propagation Delay, Positive- Going PL to Negative-Going IRF	4.0	22.0	4.0	23.0	ns ns	Figures 17, 18
t _{PLH}	Propagation Delay, Negative- Going PL to Positive-Going IRF	7.0	31.0	6.0	35.0		
t _{PLH}	Propagation Delay, Positive-Going OES to ORE	9.0	38.0	8.0	44.0	ns	
t _{PLH}	Propagation Delay Positive-IRF Going IES to Positive-Going	5.0	25.0	5.0	27.0	ns	Figure 18
t _{PHL}	Propagation Delay MR to ORE	7.0	28.0	7.0	31.0	ns	
t _{PLH}	Propagation Delay MR to IRF	5.0	27.0	5.0	30.0	ns	
t _{PZH}	Enable Time	1.0	16.0	1.0	18.0		
t _{PZL}	OE to Q ₀ -Q ₃	1.0	14.0	1.0	16.0		
t _{PHZ}	Disable Time	1.0	10.0	1.0	12.0	ns	
t _{PLZ}	OE to Q ₀ -Q ₃	1.0	23.0	1.0	30.0		
t _{PZH}	Enable Time	1.0	10.0	1.0	12.0		
t _{PZL}	Negative-Going \overline{OES} to Q_{S}	1.0	14.0	1.0	15.0	ns	
t _{PHZ}	Disable Time	1.0	10.0	1.0	12.0	115	
t _{PLZ}	Negative-Going $\overline{\text{OES}}$ to Q_S	1.0	14.0	1.0	16.0		
t _{PZH}	Enable Time	1.0	35.0	1.0	42.0	ns	
t _{PZL}	TOS to Q _S	1.0	35.0	1.0	39.0	113	
t _{DFT}	Fall-Through Time	0.2	0.9	0.2	1.0	ns	Figure 1
t _{AP}	Parallel Appearance Time ORE to Q0-Q3	-20.0	-2.0	-20.0	-2.0		
t _{AS}	Serial Appearance Time ORE to Q _S	-20.0	5.0	-20.0	5.0	ns	

		T _A = +25°C	C	$T_A = 0^{\circ}C$ to +70°C		1	
Symbol	Parameter	$V_{CC} = +5.0V$		$V_{CC} = +5.0V$		Units	Figur Numb
		Min M	Max	Min	Max	1	
t _S (H)	Setup Time, HIGH or LOW	7.0		7.0			
t _S (L)	D _S to Negative CPSI	7.0		7.0		ns	Figure
t _H (H)	Hold Time, HIGH or LOW	2.0		2.0		115	11, 1
t _H (L)	D _S to CPSI	2.0		2.0			
t _S (L)	Setup Time, LOW TTS to IRF, Serial or Parallel Mode	0.0		0.0		ns	Figur 11, 12, 18
t _S (L)	Setup Time, LOW Negative-Going ORE to Negative-Going TOS	0.0		0.0		ns	Figur 13, 1
t _S (L)	Setup Time, LOW Negative-Going IES to CPSI	8.0		9.0		- ns	Figure
t _S (L)	Setup Time, LOW Negative-Going TTS to CPSI	30.0		33.0			
t _S (H)	Setup Time, HIGH or LOW	0.0		0.0			
t _S (L)	Parallel Inputs to PL	0.0		0.0		ns	
t _H (H)	Hold Time, HIGH or LOW	4.0		4.0		115	
t _H (L)	Parallel Inputs to PL	4.0		4.0			
t _W (H)	CPSI Pulse Width	10.0		11.0			Figure 11, 12
t _W (L)	HIGH or LOW	5.0		6.0		ns	
t _W (H)	PL Pulse Width, HIGH	7.0		9.0		ns	Figur 17, 1
t _W (L)	TTS Pulse Width, LOW Serial or Parallel Mode	7.0		9.0		ns	Figur 11, 12, 14
t _W (L)	MR Pulse Width, LOW	7.0		9.0		ns	Figure
t _W (H)	TOP Pulse Width	14.0		16.0			Eine
t _W (L)	HIGH or LOW	7.0		7.0		ns	Figure
t _W (H)	CPSO Pulse Width	14.0		16.0			Figure 13, 1
t _W (L)	HIGH or LOW	7.0		7.0		ns	
t _{REC}	Recovery Time MR to Any Input	8.0		15.0		ns	Figure

